		DARD							
Operating Temperature Ra		ange	-40 ° C to 140		Storage Femperature	Range	-10 °C to		
Rating	Voltage Current		125 V AC ⁽³⁾		Storage Humidity Rang		Relative humidity 60 (Not dewed)		
			0.5 A Or			Deperating Humidity Range Relative humidity (Not dewe			
			SPEC	IFICATIO	NS				
IT	EM		TEST METHOD			REQL	JIREMENTS	QT	A
CONSTRU								-	
General Exa		Examined	d visually and with a measur	ina instrument.				×	×
Marking			d visually.	g	Accordin	g to the dra	awing.	×	×
-	CAL CHARA								-
Contact Resistance		Measured at 100 mA MAX.(DC or 1000Hz)			65mΩ	MAX.		×	- 1
Insulation Resistance		Measured at 250 V DC.		,	1000 MΩMIN.			×	-
Voltage Proof		375 V AC applied for 1 min.			No flashover or breakdown.			×	-
MECHAN	ICAL CHAR								
Mating and			d with an applicable connect	or.	Mating F	orce:	20 N MAX.	×	- 1
Unmating Forces					Unmating Force: 2.2 N MIN.				
Mechanical Operation		Mated and unmated 10 times.			(1)Contact Resistance : $75m\Omega$ MAX.			×	-
					2No damage, cracks or looseness of parts.				
Vibration		Frequency $50 \sim 100 \rightarrow 100 \sim 150 \rightarrow 150 \sim 300$ Hz					ontinuity of more than 1 μ s.	×	-
		Acceleration 98 \rightarrow 98~294 \rightarrow 294 m/s ²			②No da	mage, cracl	ks or looseness of parts.		
		1 cycle 3			1				
Shock		3 h for 3 axial directions $^{(4)}$			-				-
Shock		Acceleration 980 m/s ² , duration of pulse 6 ms at 3 times for 3 axial directions.			1			×	-
	MENTAL C								
Damp Heat	MENTALC			1000 h	(1)Conto	ot Dociotory	ce:75mΩ MAX.		1
	2)	Exposed	at 60±2 °C, 90 ~ 95 %	, 1000 h.	~		^	×	-
(Steady state) Rapid Change of		Temperature -40 → +140 °C				2Insulation Resistance : 1000 MΩ MIN. $33No damage, cracks or looseness of parts.$			+-
Temperature		Temperature $-40 \rightarrow +140 \circ C$ Time $30 \rightarrow 30 \text{ min.}$			Unud	naye, tiati	no or 1003erress of parts.	×	-
I		under 1000 cycles.			1				
			time to chamber : within 2~3 N	/IN)	1				
Cold		Exposed at -40°C, 1000 h			1)Conta	ct Resistand	ce:75mΩ MAX.	×	+-
Dry Heat		Exposed at 140°C, 1000 h			-	②No damage, cracks or looseness of parts.			<u>† </u>
Sulfur Dioxid	e	Exposed at $40\pm2^{\circ}$ C, $80\pm5^{\circ}$ RH, 25 ± 5 ppm			Contact Resistance : $75m\Omega$ MAX.			×	-
		for 96 h.		<u> </u>					
Resistance to			soldering :				ase of excessive looseness	s ×	-
Soldering Heat		Peak TMP : 260°CMAX Reflow TMP: 220°CMIN for 60sec			of the te	minal.			
Solderability			at solder temperature		A new u	niform coati	ing of solder shall cover a	×	+_
Solderability		Soldered at solder temperature $240 \pm 3^{\circ}$ C for immersion duration, 3 sec.					f the surface being	Â	
					immersed.				
					1				1
		1							
A COUN	IT D	ESCRIPTIC	ON OF REVISIONS	DES	GIGNED		CHECKED	DA	ATE
	IT D		ON OF REVISIONS F-00016361		SIGNED (. ABE		CHECKED HH. SHINDO	DA 2022	
3 1 Notes (1)) Include tempe	-DIS Parature rise	F-00016361 caused by current-carrying.	TK	(. ABE	APPROVE	HH. SHINDO		2121
3 1 Notes (1)) Include tempe (STORAGE")	–DIS Prature rise means a lo	F-00016361 caused by current-carrying. ng-term storage state for the	TK	(. ABE	APPROVE	HH. SHINDO D HH. SHINDO	2022 2019	2121 9100
3 1 Notes (1) (2)) Include tempe "STORAGE" 1 before assem	DIS- erature rise neans a lo bly to PCB	F-00016361 caused by current-carrying. ng-term storage state for the 3.	TK	(. ABE	CHECKED	HH. SHINDO D HH. SHINDO D KN. SHIBUYA	2022 2019 2019	2121 9100 9100
3 1 Notes (1) (2)	⁾ Include tempe "STORAGE" 1 before assem The creepage	DIS- erature rise neans a lo bly to PCB distance c	F-00016361 caused by current-carrying. ng-term storage state for the 3. conforms to IEC 60664-1.	TK e unused produ	(. ABE	CHECKED	HH. SHINDO D HH. SHINDO D KN. SHIBUYA D TK. ABE	2022 2019 2019 2019	2121 9100 9100 9100
3 1 Notes (1) (2) (3)	⁾ Include tempe "STORAGE" I before assem The creepage Voltage effe	DIS- erature rise neans a lo bly to PCB distance c ctive value	F-00016361 caused by current-carrying. ng-term storage state for the 3.	TK e unused produ 2	K. ABE	CHECKED	HH. SHINDO D HH. SHINDO D KN. SHIBUYA D TK. ABE	2022 2019 2019	2121 9100 9100 9100
3 1 Notes (1, (2) (3) (4)	⁾ Include tempe "STORAGE" i before assem The creepage Voltage effe Amplitude bet	DIS- erature rise means a lo bly to PCB distance c ctive value ween conn	F-00016361 caused by current-carrying. ng-term storage state for the b. conforms to IEC 60664-1. : 32V AC, Pollution Degree:	TK e unused produ 2 B is 0.05mm M	K. ABE	CHECKEE DESIGNEE DRAWN	HH. SHINDO D HH. SHINDO D KN. SHIBUYA D TK. ABE	2022 2019 2019 2019 2019 2019	2121 9100 9100 9100 9100
3 1 Notes (1, (2) (3) (4)	⁾ Include tempe "STORAGE" i before assem The creepage Voltage effe Amplitude bet ualification Tes	DIS- prature rise means a lo bly to PCB distance c ctive value ween conn st AT:Ass	F-00016361 caused by current-carrying. ng-term storage state for the conforms to IEC 60664-1. : 32V AC, Pollution Degree: ector mounting part and PC	Tk e unused produ 2 B is 0.05mm M est	(. ABE lict	CHECKEE DESIGNEE DRAWN	HH. SHINDO D HH. SHINDO D KN. SHIBUYA D TK. ABE KI. YAMAZAKI	2022 2019 2019 2019 2019 2019	2121 9100 9100 9100 9100

FORM HD0011-2-1